

Polymeric hole injection layers for perovskite-based Light-Emitting Diodes

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in
Physics

Tassilo Naujoks

Chair of Experimental Physics IV
Institute of Physics
University of Augsburg

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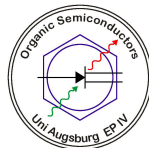
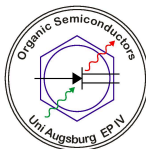


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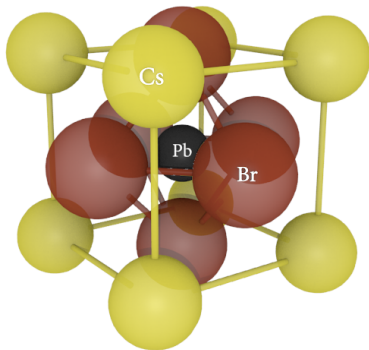
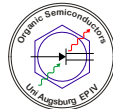
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What is a perovskite?

A perovskite is a crystal structure, that features unique dielectric properties.

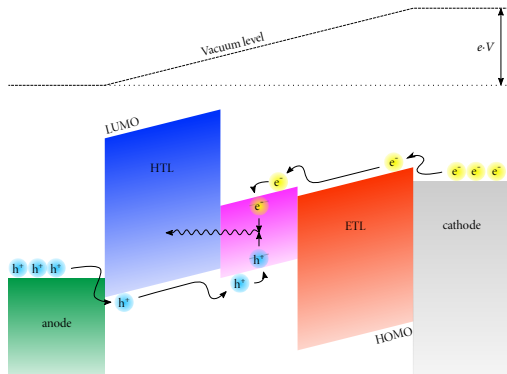


- Perovskite is the retained name for CaTiO_3 . Calling a material a perovskite refers to its crystal structure being the same as for CaTiO_3 .
- A perovskite has a structure of ABX_3 .
- Nobel price for the first high temperature super conductor.
- High electric conductivity and high absorbance.

Figure 1: Illustration of the perovskite structure with the CsPbBr_3 perovskite as example.

Basic OLED stack design

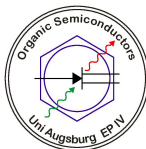
An Organic Light-Emitting Diode (OLED) consists of anode, cathode and functional organic layers in between.



- Electrons and holes are injected by the cathode and anode respectively.
- The ETL and HTL have high mobilities for the respective charge carrier.
- Charge carriers meet to form excitons, which will decay with the emission of a photon.

Figure 2: Simplified illustration of processes, leading to light emission, in OLEDs.

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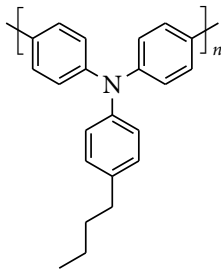


Developing a suitable hole injection site

poly-TPD has several potential advantages for application in a perovskite based OLED.



Using poly-TPD as additional HIL^a has advantages:



- Optical optimization by controlling interference effects.
- Electron blocking ability, due to a high LUMO^b.
- Dried film insoluble to most solvents.
- Enhanced hole injection properties in low HOMO^c emitting materials, enabled by a low HOMO of poly-TPD itself.
- Chemical shielding between the HIL underneath and the layer above.

Figure 3: poly-TPD

^a HIL = hole injection layer

^b LUMO = lowest unoccupied molecular orbital

^c HOMO = highest occupied molecular orbital

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Investigation on optical properties of (MA)PbI₃

The optical properties are well-suited to verify a perovskite formation.



Experimental Details:

- Precursors PbI₂ and (MA)I^a have been dissolved in DMF^b with 1 M concentration.
- Two solutions have been chosen for the experiment:
 - ▶ PbI₂ in DMF (1 M).
 - ▶ PbI₂ in DMF (1 M) and (MA)I in DMF (1 M) mixed at 1:1 ratio (volumetric).
- The solutions are spin coated at 5000 rpm for 30 seconds on glass substrates and subsequently heated to 90°C for 5 minutes.
- The reflexion and transmission is measured in air.

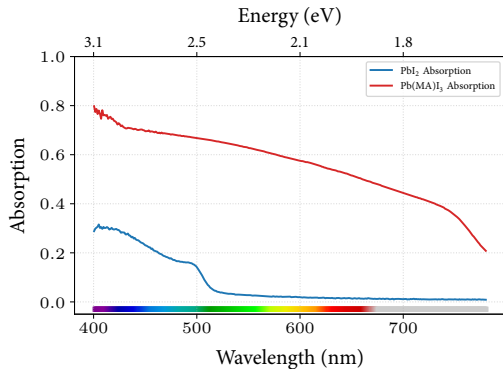
^a MA = Methylammonium

^b DMF = Dimethylformamide

Investigation on optical properties of (MA)PbI₃



The optical properties of PbI₂ are negligible for the mixed solvent's sample, indicating a full (MA)PbI₃ perovskite formation with few residual PbI₂.



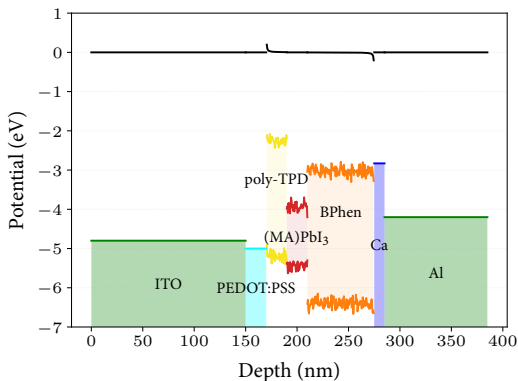
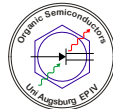
- The PbI₂ absorption: $\lambda < 500$ nm.
- The (MA)PbI₃ absorption: whole visible spectrum.
- The characteristic trait of (MA)PbI₃ to have blackish color respectively having high absorbance can be verified.^[1]

Figure 4: Absorption spectra measured by a spectrophotometer.

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Introduction of (MA)PbI₃ into an OLED stack

A standard electron injection site has been chosen, for hole injection the poly-TPD-based system has been applied.



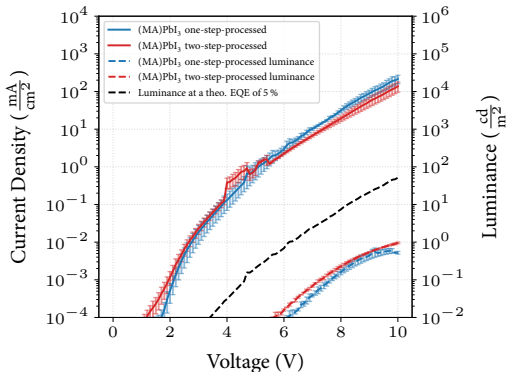
- The hole injection is performed by a PEDOT:PSS and poly-TPD layer of total thickness of 40 nm.
- The emitter is deposited by two different procedures.
 - ▶ The one-step-process: deposition by a (MA)PbI₃ solution.
 - ▶ The two-step-process: subsequent deposition of PbI₂ and (MA)I.
- For electron injection a 70 nm thick BPhen^a layer was used.

Figure 5: Schematic energy band diagram of the first (MA)PbI₃-based OLED sample.^[2-8]

^a Bathophenanthroline

Introduction of (MA)PbI₃ in an OLED stack

The (MA)PbI₃ is deposited in two different ways, yielding comparable results.

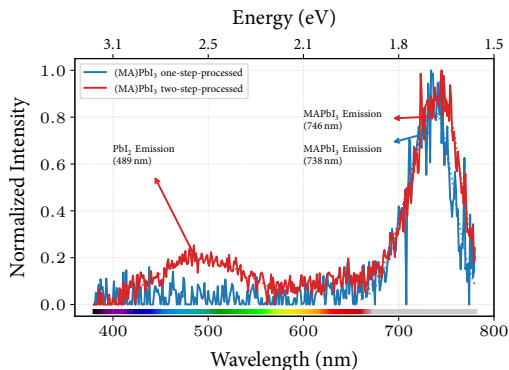


- The two-step-processed OLED shows higher luminance for lower currents.
- The OLED shows no (plain eyed) visible luminance. However devices detect a luminance.

Figure 6: Current density and luminance versus driving voltage characteristics of the (MA)PbI₃ based OLEDs.

Introduction of (MA)PbI₃ in an OLED stack

(MA)PbI₃'s luminance is at wavelengths reaching the infrared domain.



- Emission in the near infrared.
- Emission energy approx. matching HOMO-LUMO gap of 1.5 eV.
- The green emission can be ascribed to the PbI₂.

Figure 7: Electroluminescent spectrum of the (MA)PbI₃ based OLEDs.

- (MA)PbI₃ films:
 - ▶ A perovskite consisting of PbI₂ and (MA)I, (MA)PbI₃, can be synthesized.
 - ▶ The absorption of (MA)PbI₃ covers the whole spectrum, increasing towards lower wavelengths.
 - ▶ The (MA)PbI₃ surfaces are partly rough and holey.
 - ▶ Solution processing on hot grounds renders the film more closed.
- (MA)PbI₃ based OLEDs:
 - ▶ The manufactured devices work at low performance, sufficiently for a proof of concept.
 - ▶ The emission maximum is located at the visible spectrum threshold to the infrared spectrum.
 - ▶ For actual light-emitting diodes material systems like (MA)PbBr₃, are more suited to characterise.

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Characterisation of CsPbBr₃ layers

The surface texture and the layer thickness are to be determined.



Experimental Details:

- The CsPbBr₃ quantum dots are present in unknown concentration solved in toluene.
- The solution can be diluted and spin coating speeds can be adjusted.
- Layers of interest are the one grown on poly-TPD. So the standard PEDOT:PSS + poly-TPD layers are applied before spincoating the CsPbBr₃ quantum dots.
- The AFM and profilometer measurement is performed in air.

Atomic Force Microscopy of CsPbBr₃ layers

The surface texture is controlled by concentration and spin-coating speed.

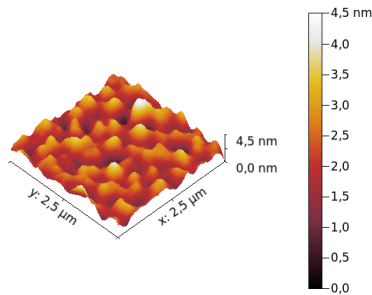


Figure 8: Surface morphology of a CsPbBr₃ quantum dots solution spin-coated at 5000 rpm on a poly-TPD coated substrate.

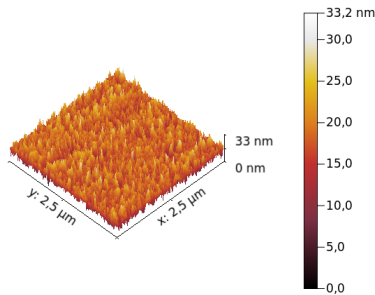
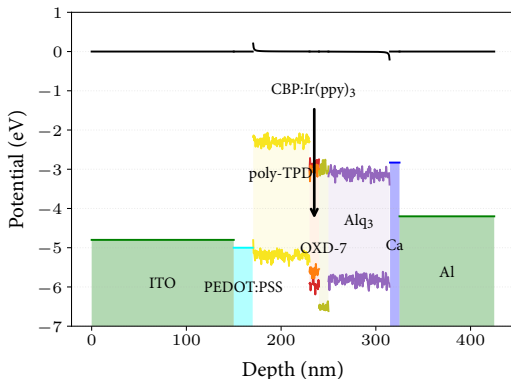
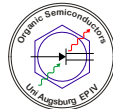


Figure 9: Surface morphology of a CsPbBr₃ quantum dots solution spin-coated at 5000 rpm on a PMMA coated substrate.

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Benchmark of the carrier injection in the OLED.

The charge carrier transport layers are tested with a well known phosphorescent emitter.



- The CBP^a:Ir(ppy)₃^b Host-Emitter system is known to have a high efficiency.
- A doping ratio of 8% Ir(ppy)₃ to CBP has been determined to be the most efficient by colleagues of the chair.

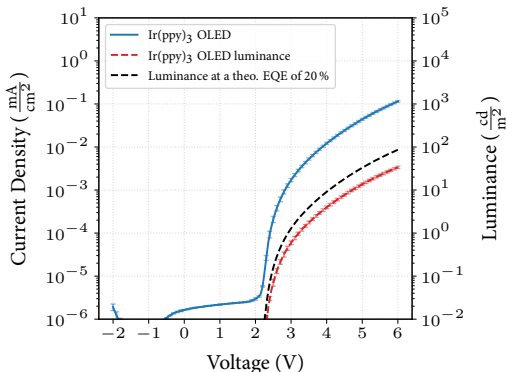
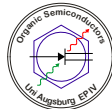
Figure 10: Schematic energy band diagram of the reference OLED sample.^[9, 10]

^a CBP = 4,4'-Bis(N-carbazolyl)-1,1'-biphenyl

^b Tris[2-phenylpyridinato-C2,N]iridium(III)

Benchmark of the carrier injection in the OLED.

The CBP:Ir(ppy)₃ device is performing well; so the charge transport layers do not inherently have an issue.



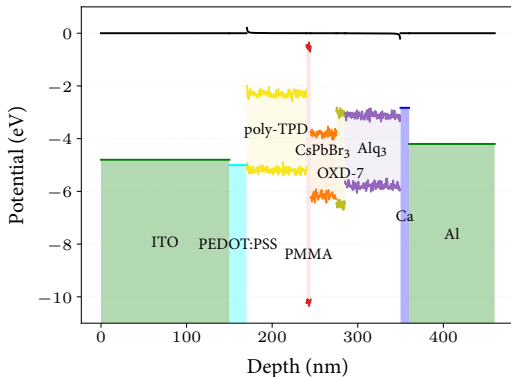
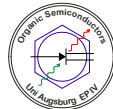
- The luminance is about half as high as the one for an ideal (isotropic) phosphorent emitter.^a
- Around the onset the sample is nearly ideal.
- No fast degradation for driving voltages up to 10 V can be observed.

Figure 11: Current density and luminance versus driving voltage characteristics of the Ir(ppy)₃-based OLED.

^a A theoretical device with a constant EQE of 20 %, the same voltage-current dependence, and the same emission spectrum.

Introduction of CsPbBr₃ in an OLED stack

For electron injection an Alq₃-OXD7 based system, and for hole injection the poly-TPD-based system has been applied.

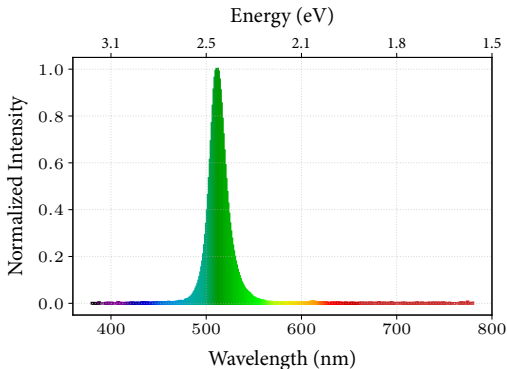


- The hole injection is performed by a PEDOT:PSS and poly-TPD layer of total thickness of 90 nm.
- An optional PMMA spacer is added to the system for better film growth.

Figure 12: Schematic energy band diagram of the first CsPbBr₃-based OLED sample.^[11, 12]

Introduction of CsPbBr₃ in an OLED stack

The CsPbBr₃ device's color is as expected a green-cyan tone.



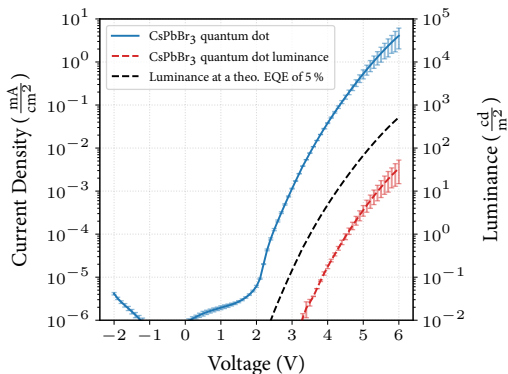
- The peak at 513 nm has a FWHM^a of approximately 20 nm, which is quite good for application in display devices.
- Other groups get very similar electroluminescent spectra.^[12–14]

Figure 13: Electroluminescent spectrum of the CsPbBr₃ based OLEDs.

^aFWHM = full width half maximum

Introduction of CsPbBr₃ in an OLED stack

The CsPbBr₃ device is not performing very well, when considering the high quantum yield of CsPbBr₃ quantum dots in general.^[15]



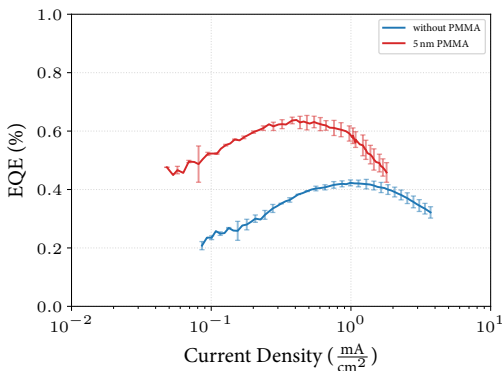
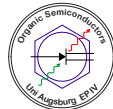
- The luminance is an order of magnitude smaller than for an ideal fluorescent emitter.^a
- The currents are two orders of magnitude higher than the ones for the Ir(ppy)₃ based device.
- The device starts degrading within seconds when driven at voltages higher than 6 volts.

Figure 14: Current density and luminance versus driving voltage characteristics of the CsPbBr₃-based OLEDs.

^a A theoretical device with a constant EQE of 5 %, the same voltage-current dependence, and the same emission spectrum.

Influence of PMMA in the CsPbBr₃-OLED

The PMMA improves the EQE of the devices by a factor of 1.5.



- The PMMA layers leads to an increased EQE.
- However, the EQEs of both devices are an order of magnitude lower than the theoretical limit.

Figure 15: EQE versus driving voltage characteristics of the CsPbBr₃-based OLEDs.

Performance of toluene-free CsPbBr₃-OLEDs

Hexane based samples achieve higher efficiencies.

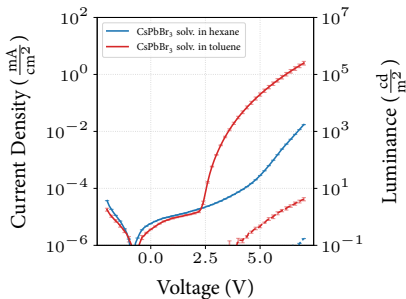


Figure 16: Current density and luminance versus driving voltage characteristics of the hexane-CsPbBr₃-based OLEDs.

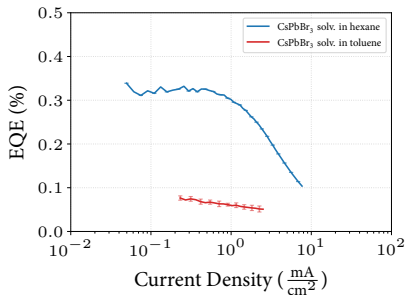


Figure 17: EQE versus driving voltage characteristics of the hexane-CsPbBr₃-based OLEDs.

- The hexane based QDs show worse injection, while showing higher EQE.

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Summary

Perovskite based OLEDs could be created. However the efficiency is very low.



- (MA)PbI₃ based OLEDs:
 - ▶ Nearly infrared light is emitted.
 - ▶ Highly depending on environmental conditions during manufacturing.
 - ▶ Very poor performance.
- CsPbBr₃ based OLEDs:
 - ▶ Green-cyan color, small peak width.
 - ▶ Impaired hole injection, which is a major shortcoming in present devices.
 - ▶ Performance depending on used solvent.

Outlook

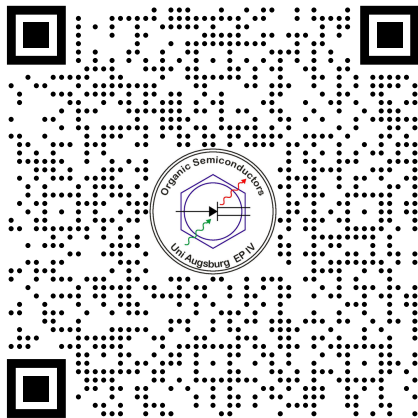
(MA)PbI₃ based OLEDs will be dropped. CsPbBr₃ based OLEDs, need further investigation.



- (MA)PbI₃ based OLEDs:
 - ▶ Switching to (MA)PbBr₃ to get actual optical devices.
 - ▶ For further investigation as IR-diode the initial results were too poor and the required equipment is not present.
- CsPbBr₃ based OLEDs:
 - ▶ Some optical measurements of the CsPbBr₃ layer may help to find other limiting factors.
 - ▶ Easing the hole-injection with new or new combination of the HILs
 - ▶ New batches of CsPbBr₃ with different solvents and ligand density should help finding a suitable hole injection system.
 - ▶ An inverted device, where ITO-ZnO is used for electron injection and hole injection can be done by well-known evaporated organics.

Thank you

Download the handout:^a



Thousand thanks to:

- Professor Wolfgang Brütting.
- Manuel Engelmayer, Florian Graßl and Thomas Morgenstern, for mentoring.
- Matthew Jurow (University of Berkeley) for supplying the CsPbBr₃ quantum dot solutions.
- All other colleagues of the Chair of Experimental Physics IV.
- and You for Your attention.

^ahttps://github.com/TassiloNaujoks/MSc/raw/master/TassiloNaujoks_MScColl_handout.pdf

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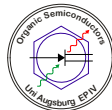
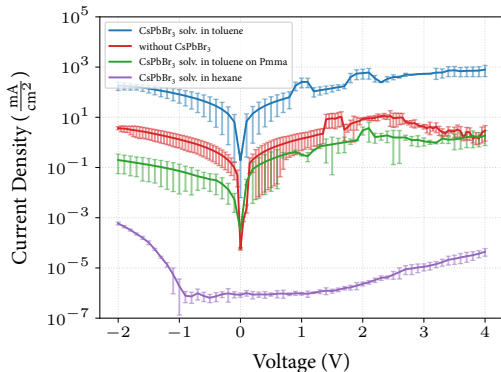
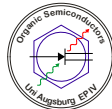


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Hole Only Devices

The hole conductivity is greatly increased by CsPbBr₃ deposition.



- The CsPbBr₃ solv. in toluene device has a resistance of only 120 Ω .
- PMMA intervenes, so that the resistance is higher than it is for the CsPbBr₃ free.
- Hexane based CsPbBr₃ devices show extremely low hole conductivity.

Figure 18: Current density versus driving voltage characteristics of hole only devices.

Solution Processed Ir(ppy)₃

The toluene susceptibility is still present, but it enhances the efficiency.

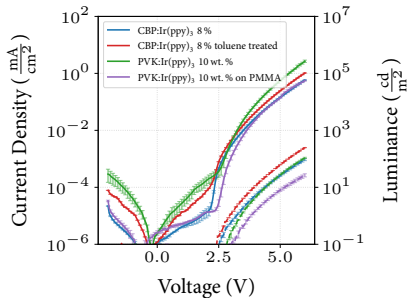
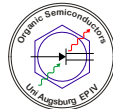


Figure 19: Current density versus driving voltage characteristics of solution processed Ir(ppy)₃ based devices.

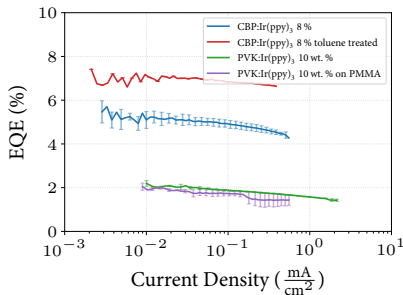
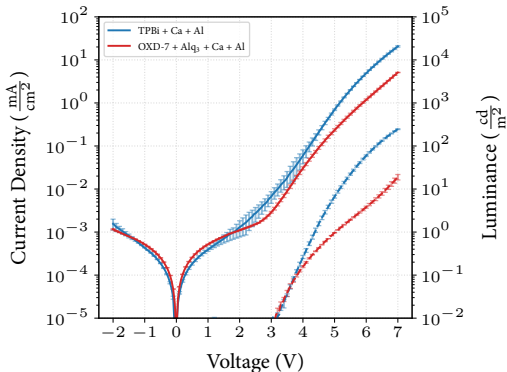
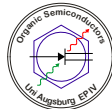


Figure 20: EQE versus current density characteristics of solution processed Ir(ppy)₃ based devices.

- PMMA does not increase the EQE, but toluene on poly-TPD does.

Switching ETL

TBPi increases the current and the luminance.



- TPBi leads to higher currents.
- But it also leads to overproportionally more luminance.
- This matter of facts contradicts the with a bad hole injection.

Figure 21: Current density versus driving voltage characteristics of TPBi based devices.

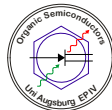
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